

SI7489DP-VB Datasheet

P-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
- 100	0.032 at $V_{GS} = - 10$ V	- 28	7.6 nC
	0.036 at $V_{GS} = - 4.5$ V	- 25	

FEATURES

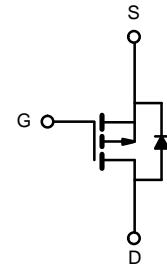
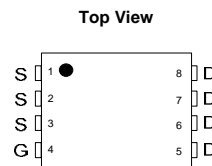
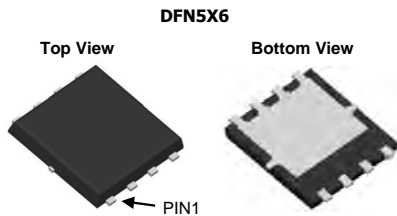
- TrenchFET[®] Power MOSFET
- 100 % UIS Tested

APPLICATIONS

- Load Switch



RoHS
COMPLIANT
HALOGEN
FREE



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	- 100	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	- 28 ^a	A
		$T_C = 70$ °C	- 27	
		$T_A = 25$ °C	22.2 ^b	
		$T_A = 70$ °C	- 26.1 ^b	
Pulsed Drain Current	I_{DM}	- 15		
Avalanche Current Pulse	I_{AS}	- 4.5	10.1	mJ
Single Pulse Avalanche Energy				
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	6.9 ^a	A
		$T_A = 25$ °C	2.1 ^b	
Maximum Power Dissipation	P_D	$T_C = 25$ °C	10.4 ^a	W
		$T_C = 70$ °C	6.6 ^a	
		$T_A = 25$ °C	1.1 ^b	
		$T_A = 70$ °C	2 ^b	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^b	R_{thJA}	33	40	°C/W	Steady State
Maximum Junction-to-Case					Steady State
	R_{thJC}	0.98	1.2		

Notes:

a. Based on $T_C = 25$ °C.

b. Surface mounted on 1" x 1" FR4 board.

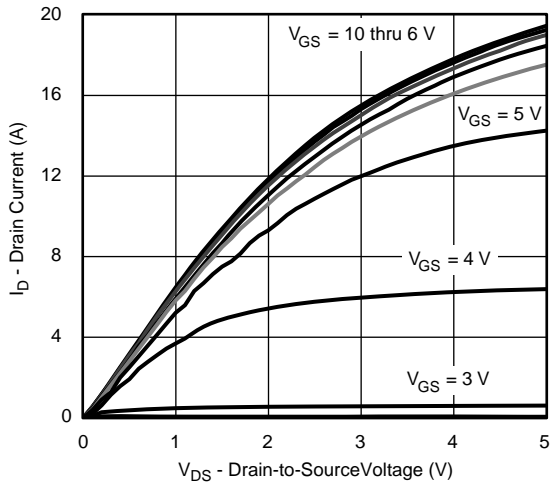
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-100			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		68		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-5.2		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1.8		-3	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	-120			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -3\text{ A}$		0.032		Ω
		$V_{GS} = -4.5\text{ V}, I_D = -2\text{ A}$		0.036		
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -5\text{ A}$	20			S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		3500		pF
Output Capacitance	C_{oss}			390		
Reverse Transfer Capacitance	C_{rss}			290		
Total Gate Charge	Q_g	$V_{DS} = -30\text{ V}, V_{GS} = -10\text{ V}, I_D = -5\text{ A}$		76	115	nC
				38	60	
Gate-Source Charge	Q_{gs}	$V_{DS} = -30\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$		16		
Gate-Drain Charge	Q_{gd}			19		
Gate Resistance	R_g	$f = 1\text{ MHz}$		5.2		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -2\text{ V}, R_L = 2\text{ }\Omega$ $I_D = -5\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		10	15	ns
Rise Time	t_r			7	15	
Turn-Off Delay Time	$t_{d(off)}$			70	110	
Fall Time	t_f			40	60	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			-6.9	A
Pulse Diode Forward Current ^a	I_{SM}				-15	
Body Diode Voltage	V_{SD}	$I_S = -3\text{ A}$		-1	-1.5	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -5\text{ A}, di/dt = 10\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		45	68	ns
Body Diode Reverse Recovery Charge	Q_{rr}			59	120	nC
Reverse Recovery Fall Time	t_a			29		ns
Reverse Recovery Rise Time	t_b			16		

Notes:

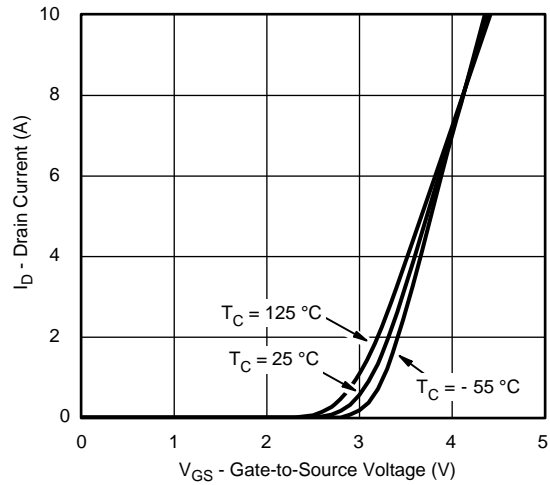
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

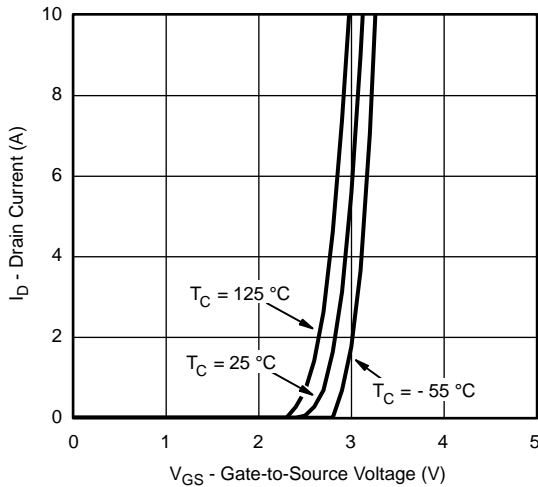
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



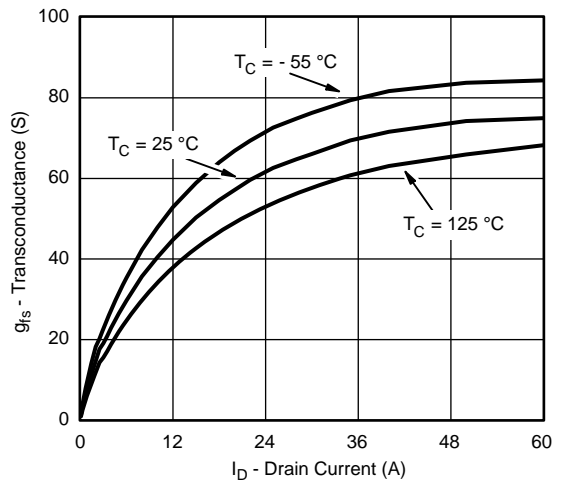
Output Characteristics



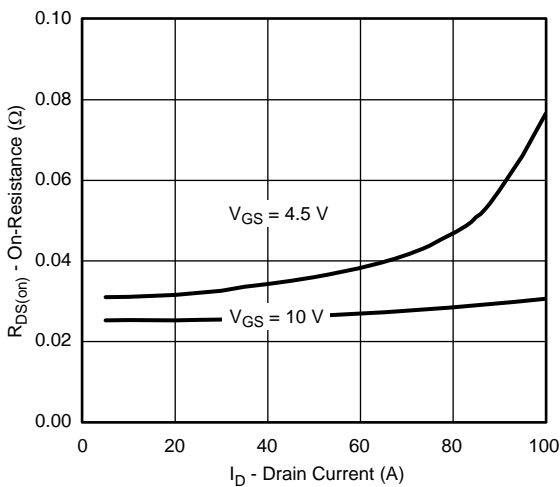
Transfer Characteristics



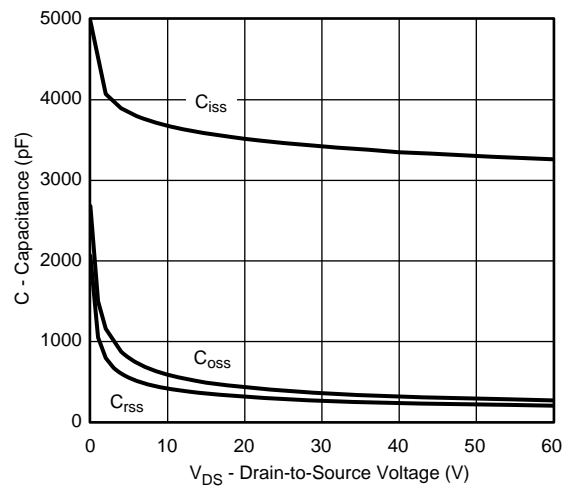
Transfer Characteristics



Transconductance

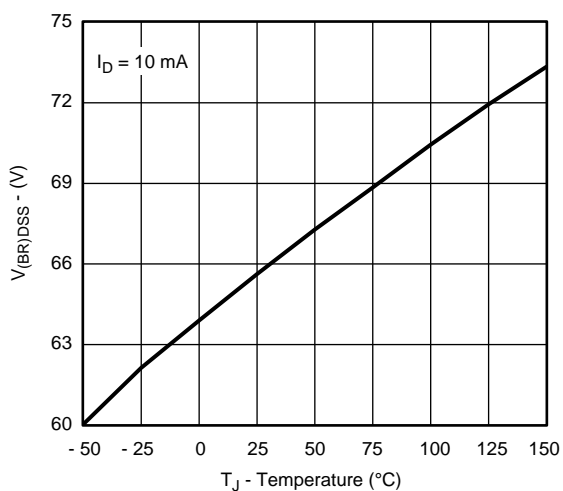
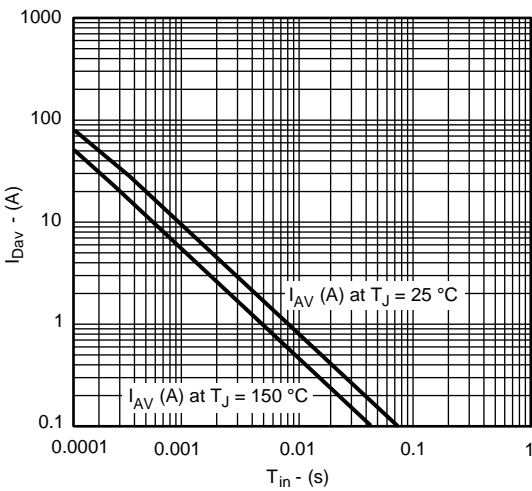
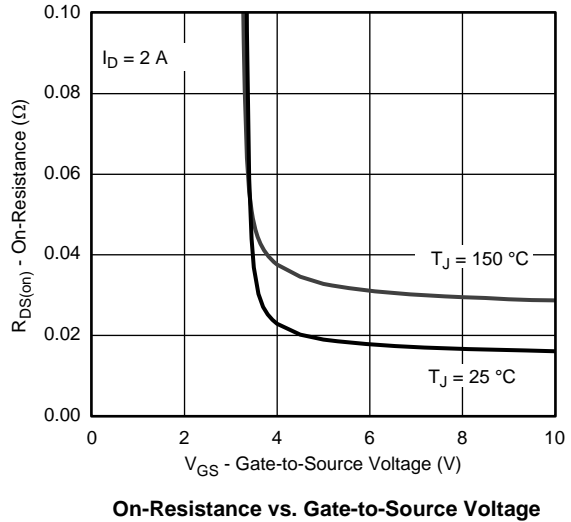
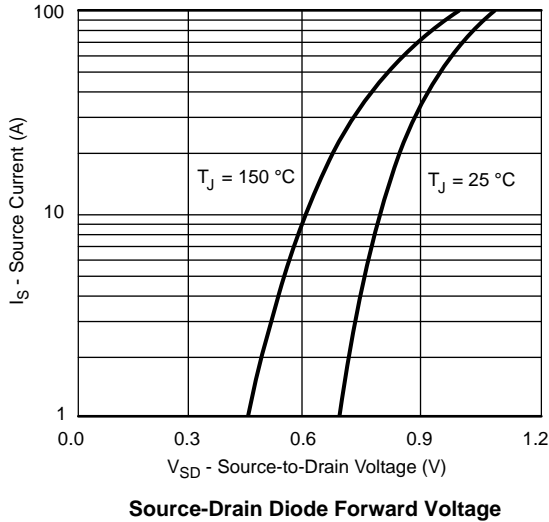
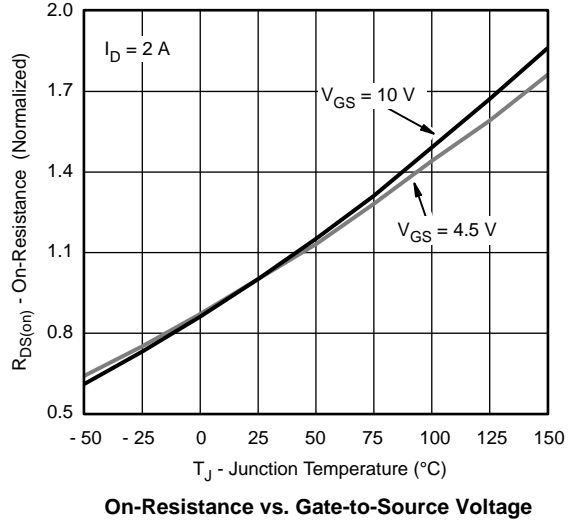
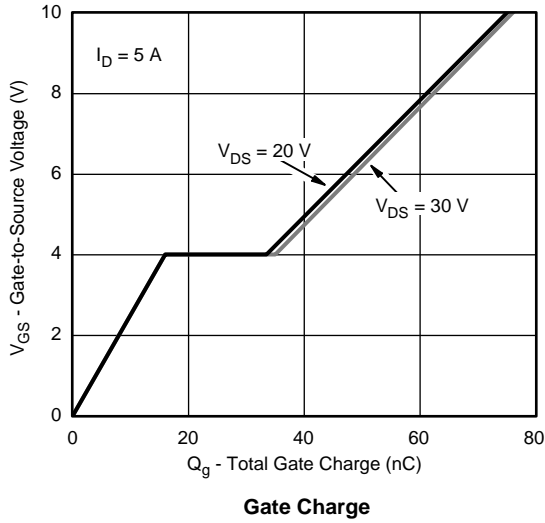


On-Resistance vs. Drain Current



Capacitance

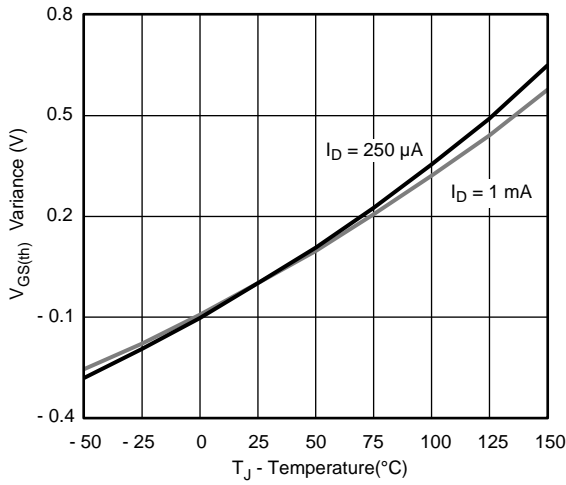
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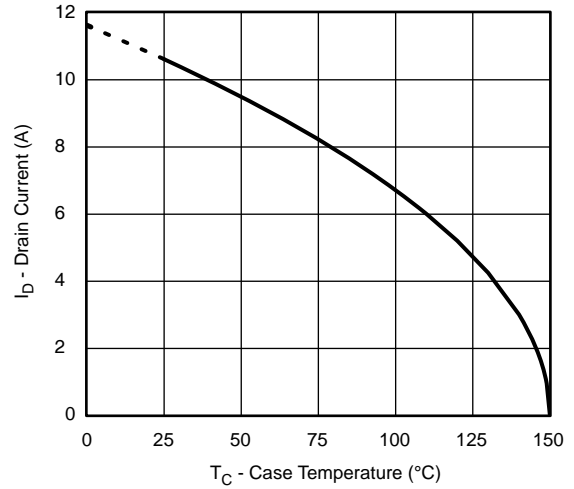
Single Pulse Avalanche Current Capability vs. Time

Drain-Source Breakdown Voltage vs. Junction Temperature

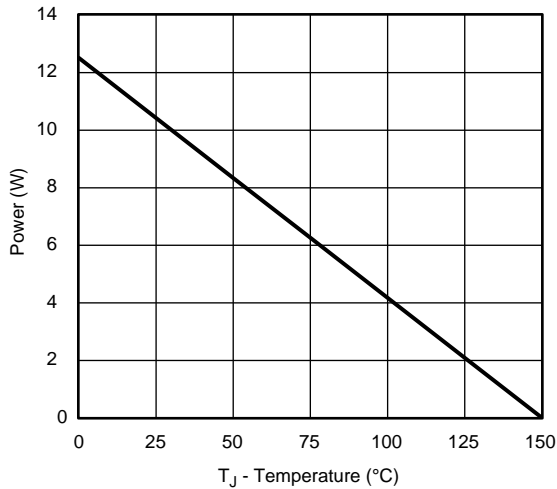
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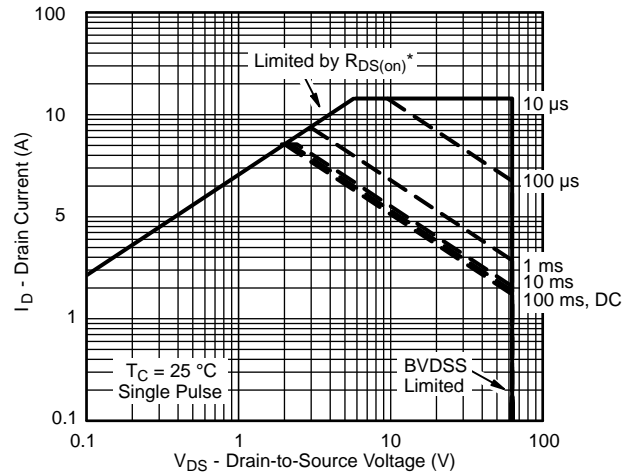
Threshold Voltage



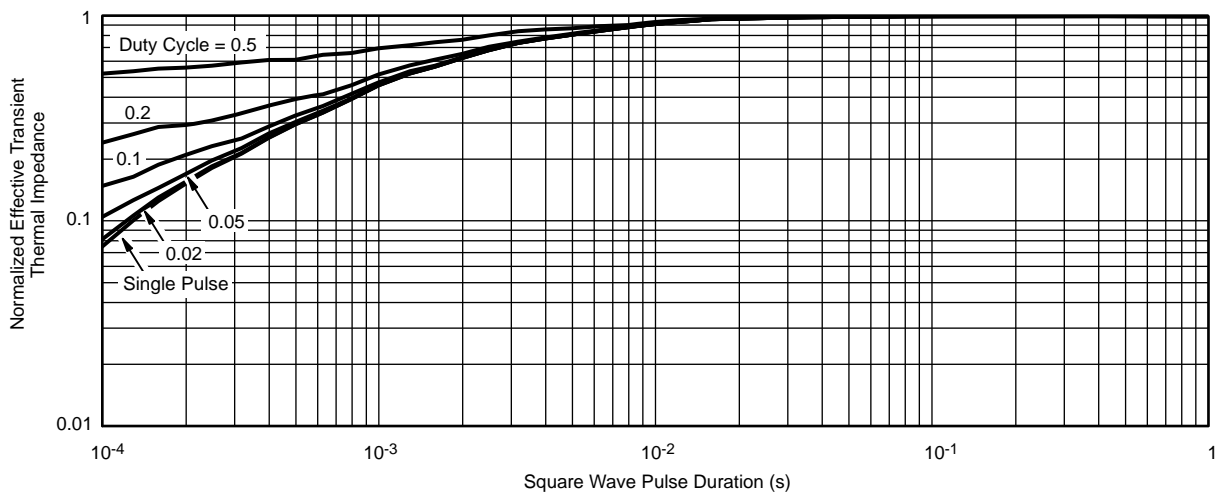
Max. Drain Current vs. Case Temperature



Power Derating, Junction-to-Case

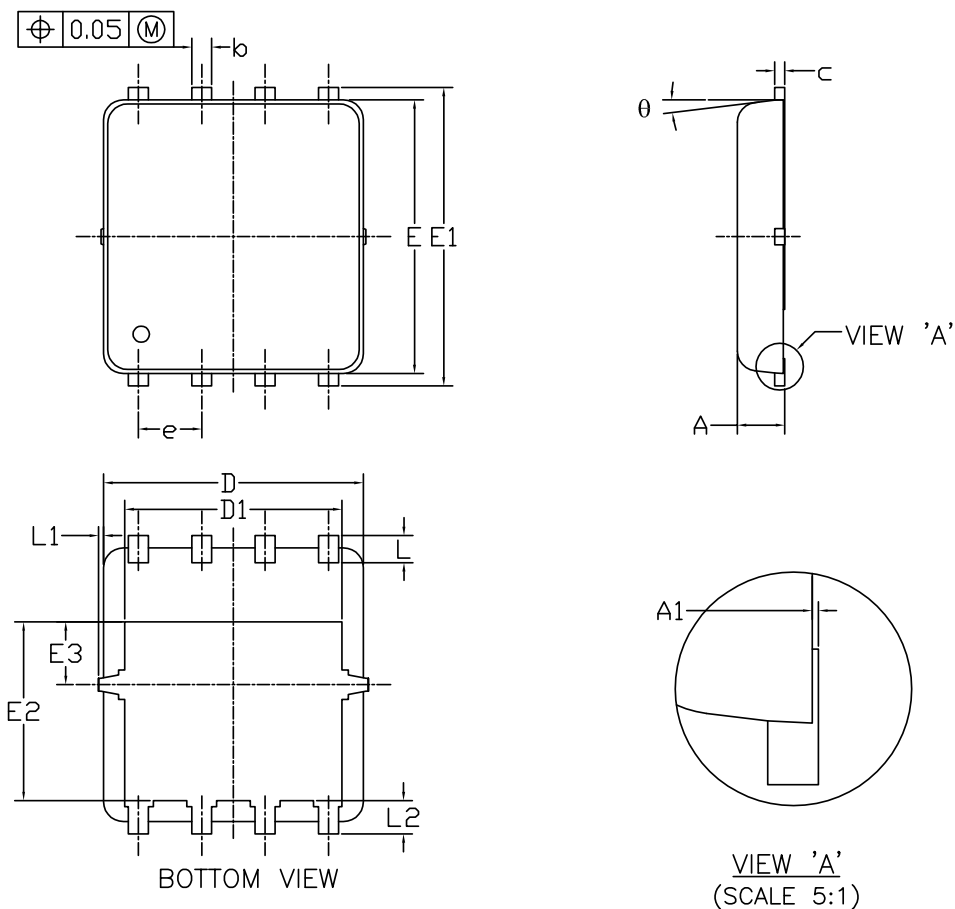


Safe Operating Area, Junction-to-Case

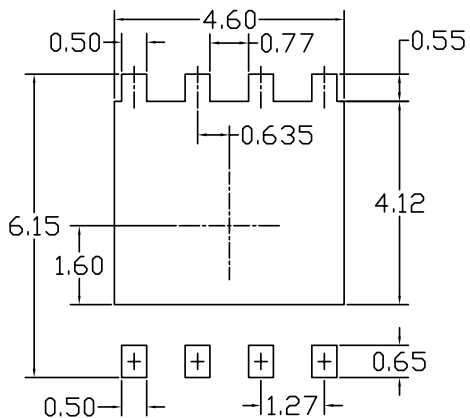


Normalized Thermal Transient Impedance, Junction-to-Case

DFN5x6_8L_EP1_P PACKAGE OUTLIN



RECOMMENDED LAND PATTERN



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.10	5.20	5.30	0.201	0.205	0.209
D1	4.25	4.35	4.45	0.167	0.171	0.175
E	5.45	5.55	5.65	0.215	0.219	0.222
E1	5.95	6.05	6.15	0.234	0.238	0.242
E2	3.525	3.625	3.725	0.139	0.143	0.147
E3	1.175	1.275	1.375	0.046	0.050	0.054
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	---	0.15	0	---	0.006
L2	0.68 REF			0.027 REF		
θ	0°	---	10°	0°	---	10°

NOTE

UNIT: mm

- PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
- CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

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